IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:) PATENT APPLICATION

Inventors: Jong-Jan Lee, Sheng Teng Hsu,

Douglas J. Tweet and Jer-Shen

Maa

Serial No.: Not Yet Assigned

Attorney Docket No. SLA 0733

Filed: Herewith

Title: STRAINED SILICON finFET

DEVICE

Honorable Commissioner for Patents Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to 37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by

the Examiner and made of record in the above-identified application.

(Date)

Respectfully submitted,

Pavid C. Ripma Reg. No. 27,672

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First Named Inventor	Jong-Jan Lee	
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Attorney Docket Number	SLA0733	

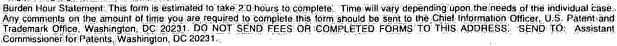
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Application Number			
Filing Date	06-23-03		
First Named Inventor	Sheng Teng Hsu		
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Attorney Docket Number	SLA0733		

OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. 1	include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
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